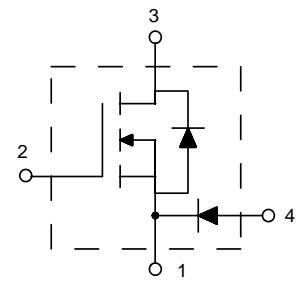
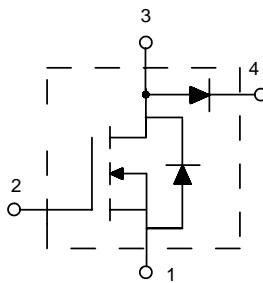
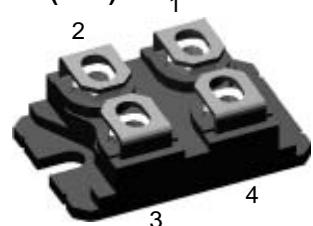


HiPerFET™
Power MOSFETs
IXFE44N50QD2 IXFE44N50QD3
IXFE48N50QD2 IXFE48N50QD3

V_{DSS}	$I_{D(\text{cont})}$	$R_{DS(\text{on})}$	t_{tr}
500 V	39 A	0.12 Ω	35 ns
500 V	41 A	0.11 Ω	35 ns

Buck & Boost Configurations for PFC & Motor Control Circuits
Preliminary data sheet


Symbol	Test Conditions	Maximum Ratings		
HiPerFET MOSFET	V_{DSS}	$T_J = 25^\circ\text{C} \text{ to } 150^\circ\text{C}$	500	V
	V_{DGR}	$T_J = 25^\circ\text{C} \text{ to } 150^\circ\text{C}; R_{GS} = 1 \text{ M}\Omega$	500	V
	V_{GS}	Continuous	±20	V
	V_{GSM}	Transient	±30	V
	I_{D25}	$T_c = 25^\circ\text{C}$	44N50Q 48N50Q	39 41 A
	I_{DM}	$T_c = 25^\circ\text{C},$ pulse width limited by max. T_{JM}	44N50Q 48N50Q	176 192 A
	I_{AR}	$T_c = 25^\circ\text{C}$		48 A
	E_{AR}	$T_c = 25^\circ\text{C}$		60 mJ
	E_{AS}	$T_c = 25^\circ\text{C}$		2.5 J
DIODE	dv/dt	$I_s \leq I_{DM}, -di/dt \leq 100 \text{ A}/\mu\text{s}, V_{DD} \leq V_{DSS},$ $T_J \leq 150^\circ\text{C}, R_G = 2 \Omega$	15	V/ns
	P_D	$T_c = 25^\circ\text{C}$	400	W
CASE	V_{RRM}		600	V
	I_{FAVM}	$T_c = 70^\circ\text{C}; \text{rectangular, } d = 0.5$	60	A
	I_{FRM}	$tp < 10 \mu\text{s}; \text{pulse width limited by } T_J$	800	A
	P_D	$T_c = 25^\circ\text{C}$	180	W
	T_J		-40 ... +150	°C
	T_{JM}		150	°C
	T_{stg}		-40 ... +150	°C
	V_{ISOL}	50/60 Hz, RMS $I_{ISOL} \leq 1 \text{ mA}$	2500 3000	V~
	M_d	Mounting torque Terminal connection torque (M4)	1.5/13 Nm/lb.in. 1.5/13 Nm/lb.in.	
Weight			19	g

ISOPLUS 227™(IXFE)


2 = Gate 3 = Drain
1 = Source 4 = Anode/Cathode

Features

- Popular Buck & Boost circuit topologies
- Conforms to SOT-227B outline
- Isolation voltage 3000 V~
- Low $R_{DS(\text{on})}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Low drain-to-case capacitance (<60 pF)
 - reduced RFI
- Ultra-fast FRED diode with soft reverse recovery

Applications

- Power factor controls and buck regulators
- DC servo and robotic drives
- DC choppers
- Switch reluctance motor controls

Advantages

- Easy to mount with 2 screws
- Space savings
- Tightly coupled FRED

Symbol	Test Conditions	Characteristic Values		
		($T_J = 25^\circ\text{C}$, unless otherwise specified)	min.	typ.
V_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 1 \text{ mA}$	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 4 \text{ mA}$	2		V
I_{GSS}	$V_{GS} = \pm 20 \text{ V}_{DC}$, $V_{DS} = 0$		± 100	nA
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0 \text{ V}$	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$	100	μA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = I_T$	44N50Q 48N50Q	0.12	Ω
		Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $\delta \leq 2 \%$	0.11	Ω

Symbol	Test Conditions	Characteristic Values		
		($T_J = 25^\circ\text{C}$, unless otherwise specified)	min.	typ.
g_{fs}	$V_{DS} = 10 \text{ V}$, $I_D = I_T$, pulse test	30	36	S
C_{iss}	$V_{GS} = 0 \text{ V}$, $V_{DS} = 25 \text{ V}$, $f = 1 \text{ MHz}$	8000		pF
C_{oss}		930		pF
C_{rss}		220		pF
$t_{d(on)}$	$V_{GS} = 10 \text{ V}$, $V_{DS} = 0.5 \text{ V}_{DSS}$, $I_D = I_T$ $R_G = 1\Omega$ (External)	33		ns
t_r		22		ns
$t_{d(off)}$		75		ns
t_f		10		ns
$Q_{g(on)}$	$V_{GS} = 10 \text{ V}$, $V_{DS} = 0.5 \text{ V}_{DSS}$, $I_D = I_T$	190		nC
Q_{gs}		40		nC
Q_{gd}		86		nC
R_{thJC}			0.31	K/W
R_{thJK}			0.07	K/W

Ultra-fast Diode

Symbol	Test Conditions	Characteristic Values		
		($T_J = 25^\circ\text{C}$, unless otherwise specified)	min.	typ.
I_R	$T_J = 25^\circ\text{C}$; $V_R = V_{RRM}$ $T_J = 150^\circ\text{C}$; $V_R = 0.8V_{RRM}$		200	μA
V_F	$I_F = 60\text{A}$, $V_{GS} = 0 \text{ V}$		2.05	V
	Note1	$T_J = 150^\circ\text{C}$	1.4	V
t_{rr}	$I_I = 1\text{A}$, $dI/dt = -200 \text{ A}/\mu\text{s}$, $V_R = 30 \text{ V}$, $T_J = 25^\circ\text{C}$	35	50	ns
I_{RM}	$I_F = 60\text{A}$, $dI/dt = -100 \text{ A}/\mu\text{s}$, $V_R = 100 \text{ V}$, $T_J = 100^\circ\text{C}$		8.3	A
R_{thJC}			0.7	K/W
R_{thJK}			0.05	K/W

Note: 1. Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $\delta \leq 2 \%$

2. IXFE44N50 $I_T = 22\text{A}$
- IXFE48N50 $I_T = 24\text{A}$

IXYS reserves the right to change limits, test conditions, and dimensions.